

IN THE CLAIMS

Please cancel claims 3, 4, 10, 11, 17 and 18.

Please amend the following claims as specified below:

✓ 1 (Amended). A method of fabricating an electrical device formed in a semiconductor substrate, said method comprising:

forming an insulating layer over said semiconductor substrate;

forming a silicon-containing structure on said insulating layer;

forming a conductive structure on said silicon-containing structure; and

oxidizing a portion of said insulating layer and said silicon-containing structure while leaving said conductive structure substantially unoxidized by introducing [an oxygen-containing gas] O_2 and [a separate hydrogen containing gas] H_2 to said insulating layer, said silicon-containing structure and said conductive structure.

Sub B2
Q4 ✓ 9 (Amended). A method of oxidizing a first feature while leaving a second feature substantially unoxidized, said method comprised of subjecting said first and second features to [an oxygen-containing gas] O_2 and [a separate hydrogen-containing gas] H_2 .

Sub B3
Q3 ✓ 16 (Amended). A method of fabricating a capacitor having a dielectric between a bottom electrode and a top electrode and situated over a semiconductor substrate, said method comprising the steps of:

providing said bottom electrode over said semiconductor substrate;

providing a dielectric material over said bottom electrode; and

subjecting said bottom electrode and said dielectric material to [an oxygen-containing gas] O_2 and [a separate hydrogen-containing gas] H_2 , wherein said

A3 dielectric material is oxidized and said bottom electrode remains substantially unoxidized.

Please add the following claims:

sub p47 -- 20 (New). The method of claim 1 wherein said oxidizing step comprises the step of oxidizing a portion of said insulating layer and said silicon-containing structure while leaving said conductive structure substantially unoxidized by introducing O₂ and H₂ in a portion of a process chamber's total volume. --

A4 -- 21 (New). The method of claim 1 wherein said oxidizing step comprises the step of oxidizing a portion of said insulating layer and said silicon-containing structure while leaving said conductive structure substantially unoxidized by introducing O₂ and H₂ in a predetermined ratio and increasing the concentration of one of said O₂ or H₂ after a reaction begins. --

sub p57 -- 22 (New). The method of claim 9 and further comprising the step of introducing O₂ and H₂ in a portion of a process chamber's total volume. --

-- 23 (New) The method of claim 9 and further comprising the step of introducing O₂ and H₂ in a predetermined ratio and increasing the concentration of one of said O₂ or H₂ after a reaction begins. --

sub p67 -- 24 (New). The method of claim 16 and further comprising the step of introducing O₂ and H₂ in a portion of a process chamber's total volume. --

-- 25 (New) The method of claim 16 and further comprising the step of introducing O₂ and H₂ in a predetermined ratio and increasing the concentration of one of said O₂ or H₂ after a reaction begins. --

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✓ -- 26 (New). A method of fabricating an electrical device formed in a semiconductor substrate, said method comprising:

- forming an insulating layer over said semiconductor substrate;
- forming a silicon-containing structure on said insulating layer;
- forming a conductive structure on said silicon-containing structure; and
- oxidizing a portion of said insulating layer and said silicon-containing structure while leaving said conductive structure substantially unoxidized by introducing an oxygen-containing gas selected from the group consisting of O₂, N₂O, CO₂ and a separate hydrogen-containing gas to said insulating layer, said silicon-containing structure and said conductive structure.--

✓ -- 27 (New). The method of claim 26 wherein said oxidizing step comprises the step of oxidizing a portion of said insulating layer and said silicon-containing structure while leaving said conductive structure substantially unoxidized by introducing said oxygen-containing gas and said hydrogen containing gas in a portion of a process chamber's total volume. --

-- 28 (New). The method of claim 26 wherein said oxidizing step comprises the step of oxidizing a portion of said insulating layer and said silicon-containing structure while leaving said conductive structure substantially unoxidized by introducing oxygen-containing gas and said hydrogen containing gas in a first